

## **ABSTRACT OF THE DISCLOSURE**

An electrostatic discharge (ESD) protection device includes a semiconductor layer, a source region formed in the layer, a drain region formed in the layer, a channel region in the layer between the source and drain regions, and a gate over the channel region. One or more islands are distributed either symmetrically or non-symmetrically in and along the drain region. The islands can be formed of polysilicon or a field oxide.